

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. SEPP15.001AUS	APPLICATION NO. 10/003,749
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Skarp et al.	
RECEIVED OCT 27 2003 U.S. PATENT & TRADEMARK OFFICE RECEIVED OCT 31 2003 TC 4700		FILING DATE October 23, 2001	GROUP 1762
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U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
1	US 2003/0129298 A1	07/10/03	Tera et al.			
2	US 2001/0031379 A1	10/18/01	Tera et al.			
3	US 2002/0003403 A1	01/10/02	Ghosh et al.			
4	US 2001/0052752 A1	12/20/01	Ghosh et al.			

FOREIGN PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
5	WO 03/008110 A1	01/30/03	PCT			YES NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
6	Kukli et al, "Atomic layer epitaxy growth of aluminum oxide thin films from a novel Al(CH ₃) ₂ Cl precursor and H ₂ O.", J. Vac. Sci. Technol. A 15(4), July/Aug 1997, pp. 2214-2218	
7	Hiltunen et al. "Growth and Characterization of Aluminum Oxide Thin Films Deposited from Various Source Materials by Atomic Layer Epitaxy and Chemical Vapor Deposition Processes", Materials Chemistry and Physics, 28 (1991) pp. 379-388	
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EXAMINER	DATE CONSIDERED
EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	